L Number	Hits	Search Text	DB	Time stamp
5	3	(("6344401") or ("6165885") or	USPAT	2004/01/12 07:56
3	3	("5834320")).PN.	USPAI	2004/01/12 07:36
_	044		HODE .	2004/01/12 00 02
6	244	(wafer and (metal adj (film or layer)) and	USPAT;	2004/01/12 08:03
		(attach\$5 or bond\$4) and ((balls adj grid	US-PGPUB;	
		adj arrays) or (BGA)) and semiconductor	EPO; JPO;	
		and (dic\$4 or cut\$4 or separat\$5)) and	DERWENT;	
		@ad<=20000616	IBM_TDB	1
7	244	(wafer and (metal adj (film or layer)) and	USPAT;	2004/01/12 08:04
		(attach\$5 or bond\$4) and ((balls adj grid	US-PGPUB;	
		adj arrays) or (BGA)) and semiconductor	EPO; JPO;	1
	:	and (dic\$4 or cut\$4 or separat\$5)) and	DERWENT;	
		@ad<=20000616	IBM TDB	
8	166	((wafer and (metal adj (film or layer))	USPĀT;	2004/01/12 08:05
]		and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616 ) and	IBM TDB	
		align\$6		
9	688	(438/455).CCLS.	USPAT;	2004/01/12 08:08
		(15071557.0026.	US-PGPUB:	2004/01/12 00.00
	<u> </u>		EPO; JPO;	İ
			DERWENT;	
			,	
12	10	438/455,456,457,458,459,460,461,462,464.ccl	IBM_TDB	2004/01/12 00:11
12	12			2004/01/12 08:11
		and (wafer and (metal adj (film or layer))	US-PGPUB;	
		and (attach\$5 or bond\$4) and ((balls adj	EPO; JPO;	
		grid adj arrays) or ("BGA")) and (dic\$4 or	DERWENT;	ĺ
		cut\$4 or separat\$5)) and @ad<=20000616	IBM_TDB	
11	97	,	USPAT;	2004/01/12 08:52
		(film or layer)) and (attach\$5 or bond\$4)	US-PGPUB;	ĺ
		and ((balls adj grid adj arrays) or	EPO; JPO;	
		("BGA")) and (dic\$4 or cut\$4 or	DERWENT;	
1		separat\$5)) and @ad<=20000616	IBM_TDB	
-	348	(438/15).CCLS.	USPAT	2004/01/12 08:08
-	258	(438/113).CCLS.	USPAT	2002/07/03 08:58
-	94	(438/110).CCLS.	USPAT	2002/07/03 08:58
-	59	(438/114).CCLS.	USPAT	2002/07/03 08:58
i <b>-</b>	681	438/15,110,113,114.ccls.	USPAT	2002/12/19 14:38
-	401	438/15,110,113,114.ccls. and test\$3	USPAT	2001/08/07 15:09
_	272	(438/15,110,113,114.ccls. and test\$3) and	USPAT	2001/08/07 15:10
1		(dice\$4 or cut\$5)		
_	901	438/15,110,113,114.ccls.	USPAT;	2002/02/04 09:53
			EPO; JPO;	,,
			DERWENT	
_	460	438/15,110,113,114.ccls. and test\$3	USPAT;	2002/02/04 09:54
		100, 10, 110, 110, 111, 0010, and 0000,	EPO; JPO;	2002,02,01 03.01
			DERWENT	
_	325	(438/15,110,113,114.ccls. and test\$3) and	USPAT;	2002/02/05 08:26
	]	(dic\$5 or cut\$5)	EPO; JPO;	2002/02/03 06:26
		(areas or eachs)	DERWENT	
_	5	(("6077757") or ("6335224") or ("6309943")		2003/10/24 12:32
'	, 3 I		USPAT	2003/10/24 12:32
_	,	or ("6309909") or ("6326697")).PN.	LICDAM	3003/03/05 00:40
-	7	(("6077757") or ("6335224") or ("6309943")	USPAT	2002/02/05 09:49
		or ("6309909") or ("6326697") or		
		("5858815") or ("5137836")).PN.		0000/00/05 55 55
-	326	(438/15,110,113,114.ccls. and test\$3) and	USPAT;	2002/02/05 08:28
		(dic\$5 or cut\$5)	EPO; JPO;	
			DERWENT	
	0	((438/15,110,113,114.ccls. and test\$3) and	USPAT;	2002/02/05 08:33
İ		(dic\$5 or cut\$5) ) and (magnet\$7 adj	EPO; JPO;	
	,	align\$5)	DERWENT	
-	170	((438/15,110,113,114.ccls. and test\$3) and	USPAT;	2002/02/05 08:32
		(dic\$5 or cut\$5) ) and (align\$5)	EPO; JPO;	
			DERWENT	
_	2705	magnet\$7 adj align\$5	USPAT;	2002/02/05 08:56
			EPO; JPO;	
			DERWENT	
_ i	ol	(magnet\$7 adj align\$5) and (wafer adj20	USPAT;	2002/02/05 08:37
	,	dielectric adj tape)	EPO; JPO;	= 352, 32, 33 33.37
	;	altitude aaj tapo/	DERWENT	
	/	<u> </u>		l

-	0	wafer adj20 dielectric adj tape	USPAT; EPO; JPO;	2002/02/05 08:37
-	0	wafer adj dielectric adj tape	DERWENT USPAT; EPO; JPO;	2002/02/05 08:38
-	248	(magnet\$7 adj align\$5) and semiconductor	DERWENT USPAT; EPO; JPO;	2002/02/05 08:57
_	0	((magnet\$7 adj align\$5) and ring) and (charged adj slot)	DERWENT USPAT; EPO; JPO;	2002/02/05 08:49
_	0	(magnet\$7 adj align\$5) and (charged adj slot)	DERWENT USPAT; EPO; JPO;	2002/02/05 08:49
_	613	(magnet\$7 adj align\$5) and ring	DERWENT USPAT; EPO; JPO;	2002/02/05 08:50
_	47	((magnet\$7 adj align\$5) and ring) and semiconductor	DERWENT USPAT; EPO; JPO;	2002/02/05 08:51
-	3066	optically adj align\$5	DERWENT USPAT; EPO; JPO;	2002/02/05 08:56
-	612	(optically adj align\$5) and semiconductor	DERWENT USPAT; EPO; JPO;	2002/02/05 08:57
-	8	(("6077757") or ("6335224") or ("6309943") or ("6309909") or ("6326697") or ("5858815") or ("5137836") or	DERWENT USPAT	2003/06/02 08:10
_	10260	("4781969")).PN. wood.inv.	USPAT; US-PGPUB;	2002/07/03 08:13
-	539	wood.inv. and alan	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/07/03 08:13
_	232	(wood.inv. and alan) and (micron adj technology)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/07/03 08:14
- -	1 425	("6268650").PN. (438/15).CCLS.	DERWENT; IBM_TDB USPAT USPAT	2002/12/20 10:24 2002/07/08 08:43
- - -	331 140 90	(438/113).CCLS. (438/110).CCLS. (438/114).CCLS.	USPAT USPAT USPAT	2002/07/08 08:57 2002/07/08 08:57 2002/07/08 08:57
- - -	425 331 140 90	(438/15).CCLS. (438/113).CCLS. (438/110).CCLS. (438/114).CCLS.	USPAT USPAT USPAT USPAT	2002/07/08 08:43 2002/07/08 08:57 2002/07/08 08:57 2002/07/08 14:32
-	13	(("6389689") or ("5977629") or ("5796170") or ("6326700") or ("6268650") or ("5858815") or ("5817535") or ("5770032") or ("4781969") or ("5073840") or ("5696033") or ("5834839") or	USPAT	2002/07/08 10:35
_	8	("6160714")).PN. (("6309909") or ("5858815") or ("5137836") or ("6077757") or ("6326697") or ("6165885") or ("5834320") or	USPAT	2002/07/09 09:56
_	0	("4781969")).PN. (wafer adj (bond\$3 or attach\$3) near4 (dielectric adj (layer or film))) same test\$3 same (cut\$4 or dic\$3 or separat\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/19 15:00

0					
test\$3 same (cut\$4 or dic\$3 or separat\$3)	-	0		1	2002/12/19 14:07
- 19 wafer adj (bond\$3 or attach\$3) near4 (dielectric adj (layer or film))					
19   wafer adj (bonds3 or attach\$3) near4 (dielectric adj (layer or film))			test\$3 same (cut\$4 or dic\$3 or separat\$3)		
19   wafer adj (bond\$3 or attach\$3) neard (dielectric adj (layer or film))					
Gielectric adj (layer or film)		10	for add /bonde2 on attache2\ noar4		2002/12/19 14:07
BEO; JFO; DERWENT; IBM TOB   Content of the conte	-	19		,	2002/12/19 14:07
C			(drefective adj (rayer of frim))	•	1
ISM TOB	•				
C					•
dislectric adj (layer or film)) same	_	0	(wafer adi (bond\$3 or attach\$3) near4		2002/12/19 14:38
cests3					
- 963   438/15,110,113,114.ccls.   USPAT   USP				EPO; JPO;	
963   438/15,110,113,114.ccls.   USPAT   USPAT   USPACE   USPAT   USPACE				DERWENT;	
- 1212 438/15,110,113,114.ccls. USPAT; USPAT					
US-PCPUB; EDC, JPO; DERWENT; IBM TOB (layer or film)) same test\$3   US-PCPUB; EDC, JPO; DERWENT; IBM TOB (layer or film)) same test\$3   US-PCPUB; EDC, JPO; DERWENT; IBM TOB (US-PCPUB; EDC), JPO; DERWENT; IBM TOB (	-				
- 0 438/15,110,113,114.ccls. and ((wafer ad) (bond\$3 or attach\$3) near4 (dielectric ad) (USPAT; USP-EQUBE, EDO; JPO; DERWENT; IBM TDB (USPAT; USPAT;	_	1212	438/15,110,113,114.ccls.	1	2002/12/19 14:38
- 0 438/15,110,113,114.ccls. and ({wafer adj (bonds3 or attachs3) near4 (dielectric adj (lsyer or film))) same test\$3				1	
0   438/15,110,113,114.ccls. and ((wafer adj ()SPÄT)   USPÄT ()USPÄT)   2002/12/19 14:40   USPÄT ()USPÄT)   2002/12/19 14:40   USPÄT ()USPÄT)   2002/12/19 14:40   USPÄT ()USPÄT)   2002/12/20 08:18   20					
- 0 438/15,110,113,114.ccls. and ((wafer adj (bond3) or attach83) near4 (dielectric adj (layer or film))) same test\$3  - 9 (wafer adj (dielectric adj (layer or film))) same test\$3  - 13 (("5834839") or ("6389689") or ("6160714") or ("5977629") or ("6326700") or ("6268650") or ("5696850") or ("569603") or ("569603") or ("5770032") or ("5796170") or ("5770032") or ("5796170") or ("5696033")).PN.  - 85 wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3))  - 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor  - 348 (wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 348 (wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 321 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 323 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 324 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 325 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 326 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 327 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 328 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) same semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) same semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) same semiconductor  - 98 ((wafer same (diele					
(bonds3 or attach83) near4 (dielectric adj   US-PGPUB; EPO; JPO; DERWENT; IBM TOB   USPAT; USPAT; U	_		   438/15 110 113 114 cole		2002/12/19 14:40
Clayer or film)) same test\$3   RFO, JFO, DERWENT; INTO D					2002/12/13 14:40
- 9 (wafer adj (dielectric adj (layer or film))) same test\$3 - 13 (("5834839") or ("6389689") or ("6160714") or ("5977629") or ("628650") or ("597626700") or ("628650") or ("5796170") or ("588015") or ("5887535") or ("5596307"). PN 85 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor - 86 (wafer same (dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor - 87 (wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO, JPO; DERWENT; IBM TDB USPAT; USPAGPUB; EPO, JPO; DERWENT;				1	
- 9 (wafer adj (dielectric adj (layer or film))) same test\$3 - 13 (("5834839") or ("6389689") or ("6160714") or ("5977629") or ("6326700") or ("6268660") or ("5858815") or ("5817535") or ("5770032") or ("5796170") or ("579032") or ("5796170") or ("59769033")).PN 85 wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor - 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor - 348 (wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor - 98 ((wafer same (dielectric adj (layer or film)) same test\$3 ) same (adjectric adj (la			(10) of film, // band cobbys/		
- 9 (wafer adj (dielectric adj (layer or film))) same test\$3  - 13 (("5834839") or ("6389689") or ("6160714") or ("5977629") or ("6326700") or ("6266550") or ("597629") or ("59685815") or ("597032") or ("5796170") or ("759670") or ("759670") or ("759670") or ("759670") or ("759670") or ("6326700") or ("6369630").P.N.  - 85 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) - 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor  - 78 (wafer same (dielectric adj (layer or film))) same test\$3  - 348 (wafer same (dielectric adj (layer or film))) same test\$3  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) sam					
Film)) same test\$3	_	9	(wafer adj (dielectric adj (layer or	· —	2002/12/20 08:18
- 13 (("5834839") or ("6389689") or ("6160714") or ("5977629") or ("6326700") or ("626650") or ("5977032") or ("5958815") or ("5817535") or ("4781969") or ("5796170") or ("4781969") or ("5073840") or ("559633")).PN.  - 85 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) - 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor  - 78 (wafer same (dielectric adj (layer or film)) same test\$3 - 348 (wafer same (dielectric adj (layer or film)) same test\$3 ) and semiconductor  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 1 (("6424023").PN 2 (("6897337") or ("5858815") or ("6389689")).PN 2 (("6897337") or ("6389689").PN 2 (("6897337") or ("6389689").PN (1611s adj grid adj arrays) or (BGA)) and semiconductor - 1 ("611s adj grid adj arrays) or (BGA)) and semiconductor - 1 ("611s adj grid adj arrays) or (BGA)) and semiconductor - 1 ("611s adj grid adj arrays) or (BGA)) and semiconductor - 1 ("611s adj grid adj arrays) or (BGA)) and semiconductor - 1 (BPAT; USPAT; USP			film))) same test\$3	US-PGPUB;	
TEM_TDB   Control   TEM_TDB   Control   Cont				EPO; JPO;	
- 13 (("5834839") or ("638689") or ("6160714") or ("5977629") or ("626850") or ("5977629") or ("5977629") or ("5817535") or ("5770032") or ("5770032") or ("57796170") or ("4781969") or ("5073840") or ("5696033")).PN.  - 85 wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)  - 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and Semiconductor  - 348 (wafer same (dielectric adj (layer or film))) same test\$3 and semiconductor  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 323 (("6424023").PN.  - 3 ("6424023").PN.  - 3 ("6389689")).PN.  - 3 (("5897337") or ("5858815") or ("6389689")).PN.  - 3 (("5897337") or ("6389689")).PN.  - 3 (("5897337") or ("6389689")).PN.  - 3 ((balls adj grid adj arrays) or (BGA)) and semiconductor  - 5 SPAT; USPAT; USPAT; USPAT; USPAT; USPAT; Semiconductor  - 10 ("6424023").PN.  - 2 (("5897337") or ("589869")).PN.  - 3 ((balls adj grid adj arrays) or (BGA)) and semiconductor  - 5 SPAT; USPAT; USPA				DERWENT;	
or ("5977629") or ("6326700") or ("6268650") or ("5858815") or ("5817535") or ("5770032") or ("5870033") or ("5870033") or ("5870033") or ("5870033") or ("5870032") or ("5870032") or ("587002") or					
("6268650") or ("5878815") or ("5817535") or ("577032") or ("5776170") or ("677032") or ("5776170") or ("4781969") or ("5073840") or ("5696033")).PN.	-	13		USPAT	2002/12/19 15:19
or ("5770032") or ("5796170") or ("4781969") or ("579632") or ("5797840") or ("5696033")).PN.  85 wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)  - 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor  - 348 (wafer same (dielectric adj (layer or film))) same test\$3 same (dielectric adj (layer or film))) same test\$3 same (dielectric adj (layer or film))) same test\$3 same (dielectric adj (layer or film))) same test\$3 same (dielectric adj (layer or film))) same test\$3 same (dielectric adj (layer or film))) same test\$3 same (dielectric adj (layer or film))) same test\$3 same (dielectric adj (layer or film))) same test\$3 same (dielectric adj (layer or film))) same test\$3 same (dielectric adj (layer or film)) same test\$3 same (dielectric adj (layer or f					•
- 85 wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)  - 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3))  - 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3))  - 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3))  - 79 (wafer same (dielectric adj (layer or film))) same test\$3  - 70 348 (wafer same (dielectric adj (layer or film))) same test\$3  - 70 322 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 70 322 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 70 322 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 71 (wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 82 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3] and semiconductor  - 98 ((wafer same (dielectric adj (layer or film))) same test\$3] and semiconductor  - 98 ((wafer same (dielectric adj (layer or film)) same test\$3] and semiconductor  - 98 ((wafer same (dielectric adj (layer or film)) same test\$3] and semiconductor  - 98 ((wafer same (dielectric adj (layer or film)) same test\$3] same dest\$3  - 98 ((wafer same (dielectric adj (layer or film)) same test\$3] same dest\$3  - 98 ((wafer same (dielectric adj (layer or film)) same test\$3  - 98 ((wafer same (dielectric adj (layer or film					
- 85 wafer same dielectric same test\$3 same (uspar; Uspar;					
- 85 wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)  - 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor  - 348 (wafer same (dielectric adj (layer or film))) same test\$3  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 1 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor)  - 1 ("6424023").PN.  - 2 (("5897337") or ("5858815") or ("6389689")).PN.  - 3 (("5897337") or ("6389689")).PN.  - 9187 ((balls adj grid adj arrays) or (BGA)) and semiconductor  - POPUB; - POP					
Cout\$3 or dic\$3 or slic\$3  US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT; US-PGPUB; EPG; JPG; DERWENT; IBM_TDB USPAT USPAT USPAT USPAT USPAT USPAT USPAT USPAT USPAT; USPAT USPAT; USPAT USPAT; USPAG; USPAT;	_	25		IISDAT.	2002/12/20 08:42
EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPĀT; USPĀT USPĀT 2002/12/20 10:24 2002/12/23 11:53 ("6389689")).PN. USPĀT USPĀT 2002/12/23 11:53 2003/05/20 07:59 USPĀT; USPĀT USPĀT; USPĀT USPĀ					2002/12/20 00:42
- 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor			(cutty of dicts of silets)		1
- 78 (wafer same dielectric same test\$3 same (cut\$3 or dic\$3 or slic\$3)) and semiconductor  - 348 (wafer same (dielectric adj (layer or film))) same test\$3  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 1 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor)  - 1 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor)  - 1 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor)  - 1 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor)  - 2 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor)  - 2 ((wafer same (dielectric adj (layer or film))) same test\$3) and semiconductor)  - 2 ((wafer same (dielectric adj (layer or film)) same test\$3) and semiconductor)  - 2 ((wafer same (dielectric adj (layer or film)) same test\$3] and semiconductor)  - 2 ((wafer same (dielectric adj (layer or film)) same test\$3] and semiconductor)  - 2 ((wafer same (dielectric adj (layer or film)) same test\$3] and semiconductor)  - 2 ((wafer same (dielectric adj (layer or film)) same test\$3] and semiconductor)  - 2 ((wafer same (dielectric adj (layer or film)) same test\$3] and semiconductor)  - 2 ((wafer same (dielectric adj (layer or film)) same test\$3] and semiconductor)  - 2 ((wafer same (dielectric adj (layer or film)) same test\$3] and semiconductor  - 2 ((wafer same (dielectric adj (layer or film) samitor samit					
Cut\$3 or dic\$3 or slic\$3)) and semiconductor   Semiconductor				IBM TDB	
Semiconductor   EPO; JPO; DERWENT; IBM TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB   USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB   USPAT;  USPAT; USPAT	-	78	(wafer same dielectric same test\$3 same	USPĀT;	2002/12/20 09:38
- 348 (wafer same (dielectric adj (layer or film))) same test\$3		:	(cut\$3 or dic\$3 or slic\$3)) and		
- 348 (wafer same (dielectric adj (layer or film))) same test\$3  - 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  - 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor)  - 1 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor)  - 1 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor)  - 1 ((wafer same (dielectric adj (layer or film)) band (cut\$3 or dic\$3)  - 1 ((wafer same (dielectric adj (layer or film)) band (cut\$3 or dic\$3)  - 1 ((wafer same (dielectric adj (layer or film)) band (wafar)  - 1 ((wafer same (dielectric adj (layer or USFAT; IBM TDB USFAT; IBM TDB USFAT (wafar)  - 1 ((wafer same (dielectric adj (layer or USFAT)) band (wafar)) band (wafar)  - 2 ((wafer same (dielectric adj (layer or USFAT); IBM TDB USFAT (wafar))  - 2 ((wafer same (dielectric adj (layer or USFAT)) band (wafar)) band (wafar)  - 2 ((wafer same (dielectric adj (layer or USFAT); USFAT (wafar))  - 2 ((wafer same (dielectric adj (layer or USFAT); USFAT (wafar))  - 2 ((wafer same (dielectric adj (layer or USFAT); USFAT)  - 2 ((wafer same (dielectric adj (layer or USFAT); USFAT)  - 2 ((wafer same (dielectric adj (layer or USFAT); USFAT)  - 2 ((wafer same (dielectric adj (layer or USFAT); USFAT)  - 2 ((wafer same (dielectric adj (layer or USFAT); USFAT)  - 2 ((wafer same (dielectric adj (layer or USFAT); USFAT)  - 2 ((wafer same (dielectric adj (layer or USFAT); USFAT)  - 2 ((wafer same (dielectric adj (layer or USFAT); USFAT)  - 2 ((wafer same (dielectric adj (layer or USFAT); USFAT)  - 3 (wafer same (dielectric adj (layer or USFAT); USFAT)  - 4 (wafer same (dielectric adj (layer or USFAT); USFAT)  - 5 (wafer same (dielectric adj (layer or USFAT); USFAT)  - 6 (wafer same (dielectric adj (layer or USFAT); USFAT)  - 6 (wafer same (dielectric adj (layer or USFAT); USFAT)  - 6 (wafer same (dielectric adj (layer or USFAT); USFAT)  - 7 (waf			semiconductor		
- 348 (wafer same (dielectric adj (layer or film))) same test\$3					
film))) same test\$3  ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor  98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor)  10		240	(maken some (dds) ===================================		2002/12/20 22 25
- 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT; USPAT 2002/12/23 11:53 ("6389689")).PN.  - 2 (("5897337") or ("6389689")).PN 9187 ((balls adj grid adj arrays) or (BGA)) and semiconductor uspat; US-PGPUB; EPO; JPO; DERWENT; US-PGPUB; EPO; JPO; DERWENT;	-	348			2002/12/20 09:35
DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; USPAT USPAT USPAT USPAT; USPAT USPAT;					
- 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT USPAT 2002/12/20 10:24 3 (("5897337") or ("5858815") or ("6389689")).PN.  2 (("5897337") or ("6389689")).PN.  3 (("5897337") or ("6389689")).PN.  4 (("5897337") or ("6389689")).PN.  5 (balls adj grid adj arrays) or (BGA)) and semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT;					
- 322 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor (USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; and (cut\$3 or dic\$3) (layer or film))) same test\$3 ) and semiconductor) (USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPĀT ("5897337") or ("5858815") or ("6389689")).PN.  2 (("5897337") or ("5858815") or ("6389689")).PN.  3 (("5897337") or ("6389689")).PN.  4 ((balls adj grid adj arrays) or (BGA)) and semiconductor (USPĀT; USPĀT; USPĀ					
film))) same test\$3 ) and semiconductor  98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor)  10 ((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor)  11 ("6424023").PN.  12 ("5897337") or ("5858815") or ("6389689")).PN.  13 (("5897337") or ("6389689")).PN.  14 (("5897337") or ("6389689")).PN.  15 ((balls adj grid adj arrays) or (BGA)) and semiconductor  16 (balls adj grid adj arrays) or (BGA)) and semiconductor  17 (BPAT (BPAT)	_	322	((wafer same (dielectric adi (laver or	· _	2002/12/20 09:38
- 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor) US-PGPUB; and (cut\$3 or dic\$3) EPO; JPO; DERWENT; IBM_TDB US-PGPUB; and (cut\$3 or dic\$3) EPO; JPO; DERWENT; IBM_TDB US-PGPUB; EPO; JPO; DERWENT; IBM_TDB US-PAT; US-PAT US-PAT;			, , , , , , , , , , , , , , , , , , , ,		
- 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor) USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT 2002/12/20 10:24 ("5897337") or ("5858815") or ("6389689")).PN 2 (("5897337") or ("6389689")).PN 2 (("5897337") or ("6389689")).PN 3 ((balls adj grid adj arrays) or (BGA)) and semiconductor USPAT 2002/12/23 11:53 2003/05/20 07:59 Semiconductor	1				
- 98 (((wafer same (dielectric adj (layer or film))) same test\$3 ) and semiconductor) USPĀT; US-PGPUB; and (cut\$3 or dic\$3) EPO; JPO; DERWENT; IBM TDB USPĀT 2002/12/20 10:24 ("5897337") or ("5858815") or ("6389689")).PN 2 (("5897337") or ("6389689")).PN 3 (("5897337") or ("6389689")).PN 4 (("5897337") or ("6389689")).PN 5 (("5897337") or ("6389689")).PN 6 (("5897337") or ("6389689")).PN 7 ((balls adj grid adj arrays) or (BGA)) and Semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT;					
film))) same test\$3 ) and semiconductor) and (cut\$3 or dic\$3)  -				_	
and (cut\$3 or dic\$3)  -	-	98	' ' '	1	2002/12/20 09:39
DERWENT; IBM_TDB USPAT; USPAT;			film))) same test\$3 ) and semiconductor)		
- 1 ("6424023").PN 3 (("5897337") or ("5858815") or ("6389689")).PN 2 (("5897337") or ("6389689")).PN 9187 ((balls adj grid adj arrays) or (BGA)) and semiconductor    USPAT   USPAT   2002/12/23 11:53   2003/05/20 07:59   2003/05/20   2003/05/20   2003/05/20   2003/05/20   2003/05/20   2003/05/20   2003/05/20   2003/05/20   2003/05/20   2003/05/20   2003/05/20   2003/05/20   2003/05/20   2003/05/20			and (cut\$3 or dic\$3)		
- 1 ("6424023").PN 3 (("5897337") or ("5858815") or ("6389689")).PN 2 (("5897337") or ("6389689")).PN 9187 ((balls adj grid adj arrays) or (BGA)) and semiconductor  Semiconductor  USPAT USPAT 2002/12/23 11:53 USPAT USPAT; US				1	
- 3 (("5897337") or ("5858815") or ("6389689")).PN 2 (("5897337") or ("6389689")).PN 9187 ((balls adj grid adj arrays) or (BGA)) and semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT;	_	1	("6424023") PN		2002/12/20 10.24
- 2 ("6389689")).PN 9187 (("5897337") or ("6389689")).PN. USPAT USPAT; Semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT;	1_				
- 2 (("5897337") or ("6389689")).PN. USPAT 2002/12/23 11:53 ((balls adj grid adj arrays) or (BGA)) and semiconductor USPAT; US-PGPUB; EPO; JPO; DERWENT;				331111	
- 9187 ((balls adj grid adj arrays) or (BGA)) and USPAT; US-PGPUB; EPO; JPO; DERWENT;	_	2		USPAT	2002/12/23 11:53
semiconductor  US-PGPUB; EPO; JPO; DERWENT;	_				
DERWENT;				1	
IBM_TDB					
	L			IBM_TDB	<u> </u>

-	4418	(((balls adj grid adj arrays) or (BGA)) and semiconductor) and (dic\$4 or cut\$4 or	USPAT; US-PGPUB;	2003/05/20 08:02
		separat\$5)	EPO; JPO;	
		-	DERWENT;	
	4476	///b-13dddddd (DCD)	IBM_TDB	2003/05/20 08:04
_	4476	(((balls adj grid adj arrays) or (BGA)) and semiconductor) and (dic\$4 or cut\$4 or	USPAT; US-PGPUB;	2003/05/20 08:04
		separat\$5 or saw\$4)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	955		USPAT;	2003/05/20 08:04
		and semiconductor) and (dic\$4 or cut\$4 or separat\$5)) and (metal adj (film or	US-PGPUB; EPO; JPO;	
		layer))	DERWENT;	
		123,027,7	IBM TDB	
-	970		USPĀT;	2003/05/20 08:04
		and semiconductor) and (dic\$4 or cut\$4 or	US-PGPUB;	
		separat\$5 or saw\$4)) and (metal adj (film	EPO; JPO; DERWENT;	
		or layer))	IBM TDB	
_	1	("20010052642").PN.	US-PGPUB	2003/05/20 08:12
-	472	wafer and (metal adj (film or layer)) and	USPAT;	2003/05/20 08:52
		(attach\$5 or bond\$4) and ((balls adj grid	US-PGPUB;	
		adj arrays) or (BGA)) and semiconductor	EPO; JPO;	
		and (dic\$4 or cut\$4 or separat\$5)	DERWENT; IBM TDB	
_	233	(wafer and (metal adj (film or layer)) and	USPAT;	2004/01/12 08:09
		(attach\$5 or bond\$4) and ((balls adj grid	US-PGPUB;	2001, 02, 12 00.03
		adj arrays) or (BGA)) and semiconductor	EPO; JPO;	
		and (dic\$4 or cut\$4 or separat\$5)) and	DERWENT;	
	212	@ad<=20000616	IBM_TDB	2003/05/21 08:23
_	212	((wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj	USPAT; US-PGPUB;	2003/05/21 08:23
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
	206	or cut\$6 or saw\$5)	110020.	2003/05/20 09:06
-	206	((wafer and (metal adj (film or layer)) and (attach\$5 or bond\$4) and ((balls adj	USPAT; US-PGPUB;	2003/05/20 09:06
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
	,	or cut\$6)	TIOD N III	2002/05/20 10 06
	1	(((wafer adj semiconductor) same (metal adj (film or layer)) same (attach\$5 or	USPAT; US-PGPUB;	2003/05/20 10:06
		bond\$4) same ((balls adj grid adj arrays)	EPO; JPO;	
		or (BGA)) same (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) same (dic\$5 or cut\$6 or	IBM_TDB	
_	212	saw\$5)) and @ad<=20000616 ((wafer and (metal adj (film or layer))	USPAT;	2003/05/21 09:00
	212	and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	2003/03/21 09:00
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
	:	separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
_	172	or cut\$6 or saw\$5)  (((wafer and (metal adj (film or layer))	USPAT;	2003/05/21 09:24
	1,2	and (attach\$5 or bond\$4) and ((balls adj	US-PGPUB;	2003/03/21 09:24
		grid adj arrays) or (BGA)) and	EPO; JPO;	
1	ļ	semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
_	92	or cut\$6 or saw\$5) ) and dic\$5 (((wafer and (metal adj (film or layer))	IISDAT.	2003/05/21 09:35
	92	and (attach\$5 or bond\$4) and ((balls adj	USPAT; US-PGPUB;	2003/03/21 09:35
		grid adj arrays) or (BGA)) and	EPO; JPO;	
		semiconductor and (dic\$4 or cut\$4 or	DERWENT;	
		separat\$5)) and @ad<=20000616) and (dic\$5	IBM_TDB	
		or cut\$6 or saw\$5) ) and (dicing or diced)		

and (attach\$5 or bond\$4) and ((balls adj grid adj arrays) or (BGA)) and EPO; JPO; semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616) and (dic\$5 or cut\$6 or saw\$5)) and (dicing or diced)) and (individual\$3 or each)	2003/05/21 09:36
grid adj arrays) or (BGA)) and EPO; JPO; semiconductor and (dic\$4 or cut\$4 or separat\$5)) and @ad<=20000616) and (dic\$5 or cut\$6 or saw\$5)) and (dicing or diced)) and (individual\$3 or each)	
semiconductor and (dic\$4 or cut\$4 or perwent; separat\$5)) and @ad<=20000616) and (dic\$5 IBM_TDB or cut\$6 or saw\$5)) and (dicing or diced)) and (individual\$3 or each)	
separat\$5)) and @ad<=20000616) and (dic\$5   IBM_TDB or cut\$6 or saw\$5) ) and (dicing or diced)) and (individual\$3 or each)	
or cut\$6 or saw\$5) ) and (dicing or diced)) and (individual\$3 or each)	
diced)) and (individual\$3 or each)	
- 70 ((((wafer and (metal adj (film or layer)) USPAT;	2003/05/21 09:36
and (attach\$5 or bond\$4) and ((balls adj US-PGPUB;	
grid adj arrays) or (BGA)) and EPO; JPO;	
semiconductor and (dic\$4 or cut\$4 or DERWENT;	
separat\$5)) and @ad<=20000616) and (dic\$5   IBM TDB	
or cut\$6 or saw\$5) ) and (dicing or	
diced)) and (individual\$3)	
	2003/05/21 09:37
and (attach\$5 or bond\$4) and ((balls adj US-PGPUB;	2003,03,21 03.3,
grid adj arrays) or (BGA)) and EPO; JPO;	
semiconductor and (dic\$4 or cut\$4 or DERWENT;	
separat\$5)) and @ad<=20000616) and (dic\$5   IBM TDB	
or cut\$6 or saw\$5) ) and (dicing or	
diced)) and (individual\$3 adj device)	2024/01/12 27 56
	2004/01/12 07:56
	2004/01/12 08:10
(attach\$5 or bond\$4) and ((balls adj grid US-PGPUB;	
adj arrays) or ("BGA")) and semiconductor   EPO; JPO;	
and (dic\$4 or cut\$4 or separat\$5)) and DERWENT;	
	2003/10/23 10:36
same (attach\$5 or bond\$4) same ((balls adj   US-PGPUB;	
grid adj arrays) or ("BGA")) same EPO; JPO;	
semiconductor same (dic\$4 or cut\$4 or DERWENT;	
separat\$5))) and @ad<=20000616	
- 2 (("6153448") or ("20020011859")).PN. USPĀT; 2	2003/10/24 12:35
US-PGPUB US-PGPUB	
- 4 (("6153448") or ("20020011859") or USPAT;	2003/10/24 14:07
("6064217") or ("5475317")).PN. US-PGPUB	